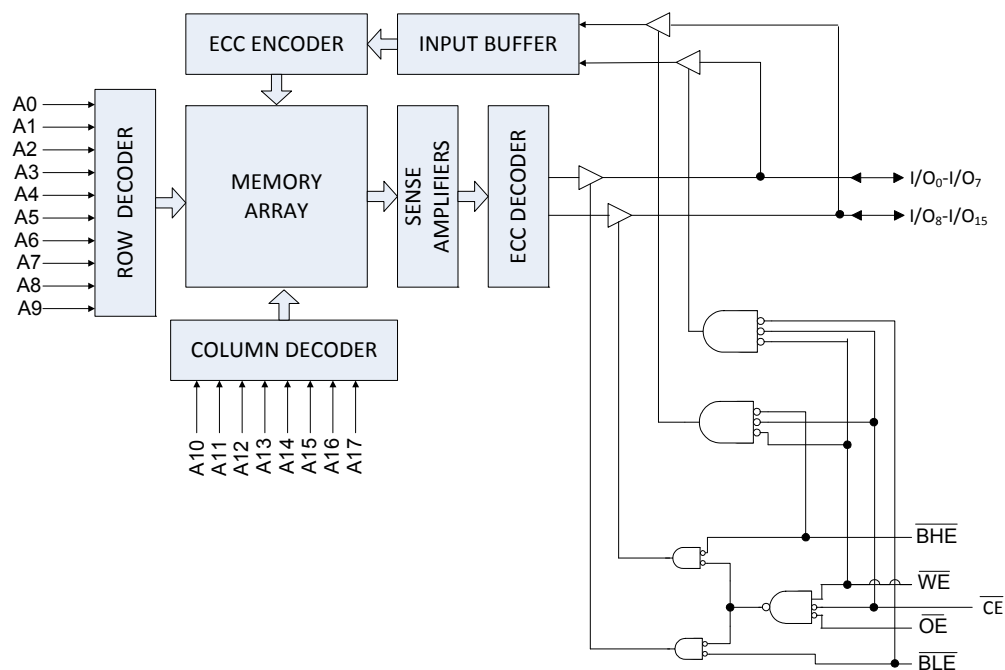


Logic Block Diagram – CY62146G

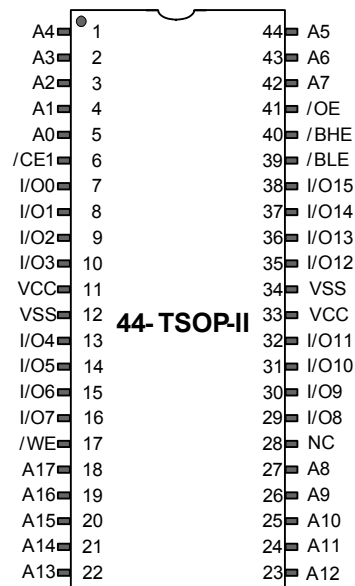


Contents

Pin Configuration – CY62146G	4	Ordering Code Definitions	15
Maximum Ratings	5	Package Diagrams	16
Operating Range	5	Acronyms	17
DC Electrical Characteristics	5	Document Conventions	17
Capacitance	7	Units of Measure	17
Thermal Resistance	7	Document History Page	18
AC Test Loads and Waveforms	7	Sales, Solutions, and Legal Information	19
Data Retention Characteristics	8	Worldwide Sales and Design Support	19
Data Retention Waveform	8	Products	19
AC Switching Characteristics	9	PSoC@Solutions	19
Switching Waveforms	10	Cypress Developer Community	19
Truth Table – CY62146G	14	Technical Support	19
Ordering Information	15		

Pin Configuration – CY62146G

Figure 1. 44-pin TSOP II pinout – CY62146G ^[3]



Note

3. NC pins are not connected internally to the die and are typically used for address expansion to a higher-density device. Refer to the respective datasheets for pin configuration.

Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

Storage temperature -65 °C to + 150 °C

Ambient temperature
with power applied -55 °C to + 125 °C

Supply voltage
to ground potential^[4] -0.3 V to $V_{CC} + 0.3$ V

DC voltage applied to outputs
in HI-Z state^[4] -0.3 V to $V_{CC} + 0.3$ V

DC input voltage^[4] -0.3 V to $V_{CC} + 0.3$ V

Output current into outputs (in low state) 20 mA

Static discharge voltage
(MIL-STD-883, Method 3015) >2001 V

Latch-up current >140 mA

Operating Range

Grade	Ambient Temperature	V_{CC}
Automotive-A	-40 °C to +85 °C	2.2 V to 3.6 V
		4.5 V to 5.5 V

DC Electrical Characteristics

Over the operating range

Parameter	Description	Test Conditions	45 ns (Automotive-A)			Unit
			Min	Typ	Max	
V_{OH}	Output HIGH voltage	2.2 V to 2.7 V $V_{CC} = \text{Min}, I_{OH} = -0.1 \text{ mA}$	2	—	—	V
		2.7 V to 3.6 V $V_{CC} = \text{Min}, I_{OH} = -1.0 \text{ mA}$	2.4	—	—	
		4.5 V to 5.5 V $V_{CC} = \text{Min}, I_{OH} = -1.0 \text{ mA}$	2.4	—	—	
		4.5 V to 5.5 V $V_{CC} = \text{Min}, I_{OH} = -0.1 \text{ mA}$	$V_{CC} - 0.5^{[5]}$	—	—	
V_{OL}	Output LOW voltage	2.2 V to 2.7 V $V_{CC} = \text{Min}, I_{OL} = 0.1 \text{ mA}$	—	—	0.4	V
		2.7 V to 3.6 V $V_{CC} = \text{Min}, I_{OL} = 2.1 \text{ mA}$	—	—	0.4	
		4.5 V to 5.5 V $V_{CC} = \text{Min}, I_{OL} = 2.1 \text{ mA}$	—	—	0.4	
V_{IH}	Input HIGH voltage	2.2 V to 2.7 V —	1.8	—	$V_{CC} + 0.3^{[4]}$	V
		2.7 V to 3.6 V —	2	—	$V_{CC} + 0.3^{[4]}$	
		4.5 V to 5.5 V —	2.2	—	$V_{CC} + 0.5^{[4]}$	
V_{IL}	Input LOW voltage	2.2 V to 2.7 V —	-0.3 ^[4]	—	0.6	V
		2.7 V to 3.6 V —	-0.3 ^[4]	—	0.8	
		4.5 V to 5.5 V —	-0.5 ^[4]	—	0.8	
I_{IX}	Input leakage current	$GND \leq V_{IN} \leq V_{CC}$	-1	—	+1	μA
I_{OZ}	Output leakage current	$GND \leq V_{OUT} \leq V_{CC}$, Output disabled	-1	—	+1	μA
I_{CC}	V_{CC} operating supply current	Max V_{CC} , $I_{OUT} = 0 \text{ mA}$, CMOS levels	$f = f_{MAX}$	—	15	mA
			$f = 1 \text{ MHz}$	—	3.5	

Note

- $V_{IL(\text{min})} = -2.0 \text{ V}$ and $V_{IH(\text{max})} = V_{CC} + 2 \text{ V}$ for pulse durations of less than 20 ns.
- This parameter is guaranteed by design and not tested.

DC Electrical Characteristics (continued)

Over the operating range

Parameter	Description	Test Conditions	45 ns (Automotive-A)			Unit
			Min	Typ	Max	
$I_{SB1}^{[6]}$	Automatic power down current – CMOS inputs; $V_{CC} = 2.2\text{ V to }3.6\text{ V and }4.5\text{ V to }5.5\text{ V}$	$\overline{CE}_1 \geq V_{CC} - 0.2\text{ V or }CE_2 \leq 0.2\text{ V}$ $V_{IN} \geq V_{CC} - 0.2\text{ V or }V_{IN} \leq 0.2\text{ V},$ $f = f_{max}$ (address and data only), $f = 0$ (\overline{OE} , \overline{WE} , \overline{BHE} , and \overline{BLE}), Max V_{CC}	–	3.5	8.7	μA
$I_{SB2}^{[6]}$	Automatic power down current – CMOS inputs $V_{CC} = 2.2\text{ V to }3.6\text{ V and }4.5\text{ V to }5.5\text{ V}$	$\overline{CE}_1 \geq V_{CC} - 0.2\text{ V or }CE_2 \leq 0.2\text{ V}$ $V_{IN} \geq V_{CC} - 0.2\text{ V or }V_{IN} \leq 0.2\text{ V},$ $f = 0$, Max V_{CC}	–	3.5	8.7	μA

Notes

 6. Chip enable (\overline{CE}) must be tied to CMOS levels to meet the $I_{SB1}/I_{SB2}/I_{CCDR}$ spec. Other inputs can be left floating.

Capacitance

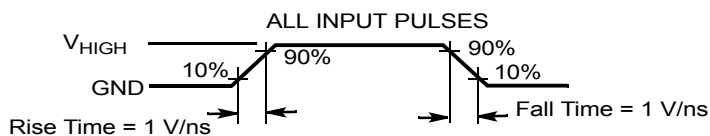
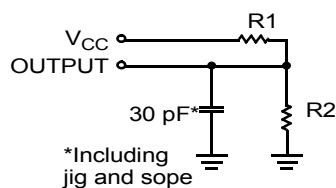
Parameter ^[7]	Description	Test Conditions	Max	Unit
C_{IN}	Input capacitance	$T_A = 25\text{ }^{\circ}\text{C}$, $f = 1\text{ MHz}$, $V_{CC} = V_{CC(\text{typ})}$	10	pF
C_{OUT}	Output capacitance		10	pF

Thermal Resistance

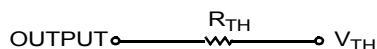
Parameter ^[7]	Description	Test Conditions	44-pin TSOP II	Unit
Θ_{JA}	Thermal resistance (junction to ambient)	Still air, soldered on a 3×4.5 inch, four-layer printed circuit board	66.82	$^{\circ}\text{C/W}$
Θ_{JC}	Thermal resistance (junction to case)		15.97	$^{\circ}\text{C/W}$

AC Test Loads and Waveforms

Figure 2. AC Test Loads and Waveforms^[8]



Equivalent to: THÉVENIN EQUIVALENT



Parameters	2.5 V	3.0 V	Unit
R1	16667	1103	Ω
R2	15385	1554	Ω
R_{TH}	8000	645	Ω
V_{TH}	1.20	1.75	V

Notes

- Tested initially and after any design or process changes that may affect these parameters.
- Full-device operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(\text{min})} \geq 100\text{ }\mu\text{s}$ or stable at $V_{CC(\text{min})} \geq 100\text{ }\mu\text{s}$.

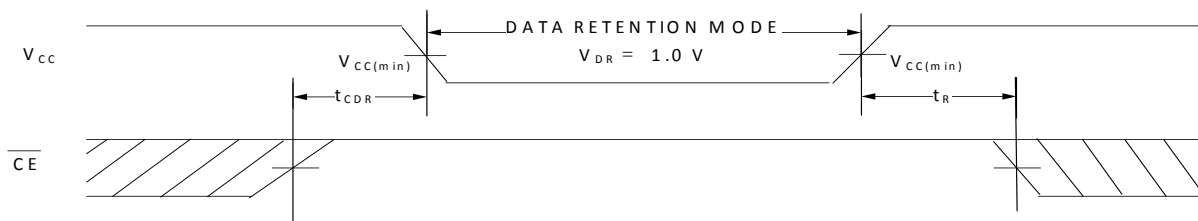
Data Retention Characteristics

Over the Operating range

Parameter	Description	Conditions (Automotive-A)	Min	Typ ^[9]	Max	Unit
V_{DR}	V_{CC} for data retention	–	1	–	–	V
$I_{CCDR}^{[10, 11]}$	Data retention current	$V_{CC} = 1.2\text{ V}$ $\overline{CE}_1 \geq V_{CC} - 0.2\text{ V}$ or $CE_2 \leq 0.2\text{ V}$, $V_{IN} \geq V_{CC} - 0.2\text{ V}$ or $V_{IN} \leq 0.2\text{ V}$	–	–	13	μA
$t_{CDR}^{[12]}$	Chip deselect to data retention time	–	0	–	–	ns
$t_R^{[12, 13]}$	Operation recovery time	–	45	–	–	ns

Data Retention Waveform

Figure 3. Data Retention Waveform



Notes

9. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = 3\text{ V}$ (for V_{CC} range of 2.2 V–3.6 V) and $V_{CC} = 5\text{ V}$ (for V_{CC} range of 4.5 V–5.5 V), $T_A = 25^\circ\text{C}$.
10. Chip enable (\overline{CE}) must be tied to CMOS levels to meet the I_{SB1} / I_{SB2} / I_{CCDR} spec. Other inputs can be left floating.
11. I_{CCDR} is guaranteed only after device is first powered up to $V_{CC(min)}$ and then brought down to V_{DR} .
12. These parameters are guaranteed by design.
13. Full-device operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min)} \geq 100\text{ }\mu\text{s}$ or stable at $V_{CC(min)} \geq 100\text{ }\mu\text{s}$.

AC Switching Characteristics

Parameter ^[14]	Description	45 ns		Unit
		Min	Max	
Read Cycle				
t _{RC}	Read cycle time	45	–	ns
t _{AA}	Address to data valid	–	45	ns
t _{OHA}	Data hold from address change	10	–	ns
t _{ACE}	\overline{CE}_1 LOW and CE ₂ HIGH to data valid	–	45	ns
t _{DOE}	\overline{OE} LOW to data valid	–	22	ns
t _{LZOE}	\overline{OE} LOW to Low impedance ^[15, 16]	5	–	ns
t _{HZOE}	\overline{OE} HIGH to HI-Z ^[15, 16, 17]	–	18	ns
t _{LZCE}	\overline{CE}_1 LOW and CE ₂ HIGH to Low impedance ^[15, 16]	10	–	ns
t _{HZCE}	\overline{CE}_1 HIGH and CE ₂ LOW to HI-Z ^[15, 16, 17]	–	18	ns
t _{PU}	\overline{CE}_1 LOW and CE ₂ HIGH to power-up ^[16]	0	–	ns
t _{PD}	\overline{CE}_1 HIGH and CE ₂ LOW to power-down ^[16]	–	45	ns
t _{DBE}	\overline{BLE} / \overline{BHE} LOW to data valid	–	22	ns
t _{LZBE}	\overline{BLE} / \overline{BHE} LOW to Low impedance ^[15, 16]	5	–	ns
t _{HZBE}	\overline{BLE} / \overline{BHE} HIGH to HI-Z ^[15, 16, 17]	–	18	ns
Write Cycle ^[18, 19]				
t _{WC}	Write cycle time	45	–	ns
t _{SCE}	\overline{CE}_1 LOW and CE ₂ HIGH to write end	35	–	ns
t _{AW}	Address setup to write end	35	–	ns
t _{HA}	Address hold from write end	0	–	ns
t _{SA}	Address setup to write start	0	–	ns
t _{PWE}	\overline{WE} pulse width	35	–	ns
t _{BW}	\overline{BLE} / \overline{BHE} LOW to write end	35	–	ns
t _{SD}	Data setup to write end	25	–	ns
t _{HD}	Data hold from write end	0	–	ns
t _{HZWE}	\overline{WE} LOW to HI-Z ^[15, 16, 17]	–	18	ns
t _{LZWE}	\overline{WE} HIGH to Low impedance ^[15, 16]	10	–	ns

Notes

14. Test conditions assume a signal transition time (rise/fall) of 3 ns or less, timing reference levels of 1.5 V (for $V_{CC} \geq 3$ V) and $V_{CC}/2$ (for $V_{CC} < 3$ V), and input pulse levels of 0 to 3 V (for $V_{CC} \geq 3$ V) and 0 to V_{CC} (for $V_{CC} < 3$ V). Test conditions for the read cycle use output loading shown in AC Test Loads and Waveforms section, unless specified otherwise.

15. At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZBE} is less than t_{LZBE} , t_{HZOE} is less than t_{LZOE} , and t_{HZWE} is less than t_{LZWE} for any device.

16. These parameters are guaranteed by design.

17. t_{HZOE} , t_{HZCE} , t_{HZBE} , and t_{HZWE} transitions are measured when the outputs enter a high-impedance state.

18. The internal write time of the memory is defined by the overlap of $\overline{WE} = V_{IL}$, $\overline{CE}_1 = V_{IL}$, and $CE_2 = V_{IH}$. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.

19. The minimum pulse width in Write Cycle No. 3 (\overline{WE} Controlled, \overline{OE} LOW) should be equal to sum of t_{SD} and t_{HZWE} .

Switching Waveforms

Figure 4. Read Cycle No. 1 of CY62146G (Address Transition Controlled) [20]

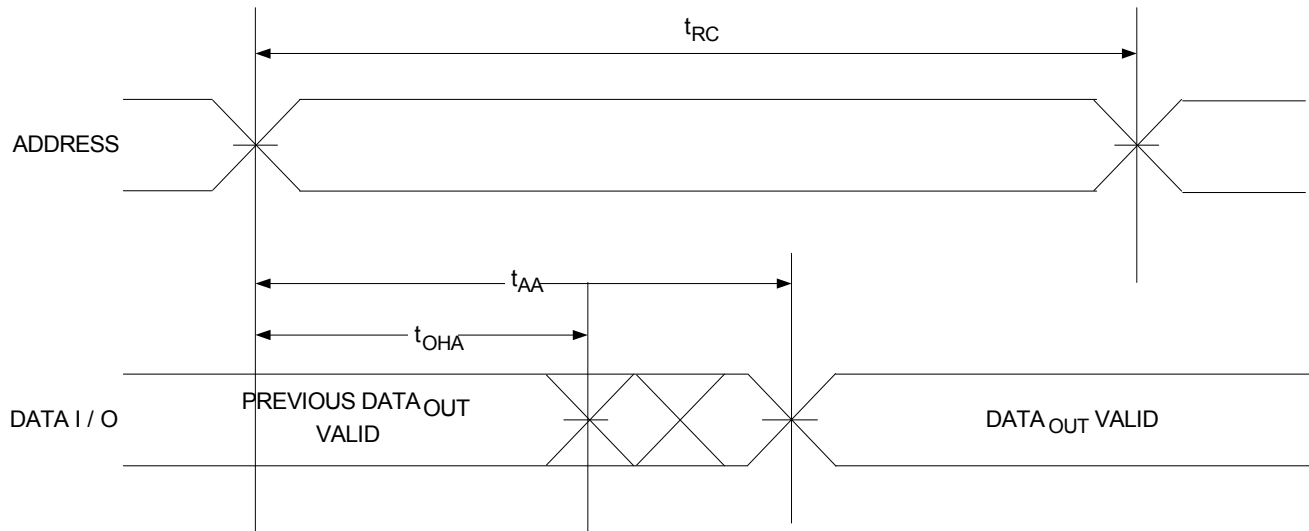
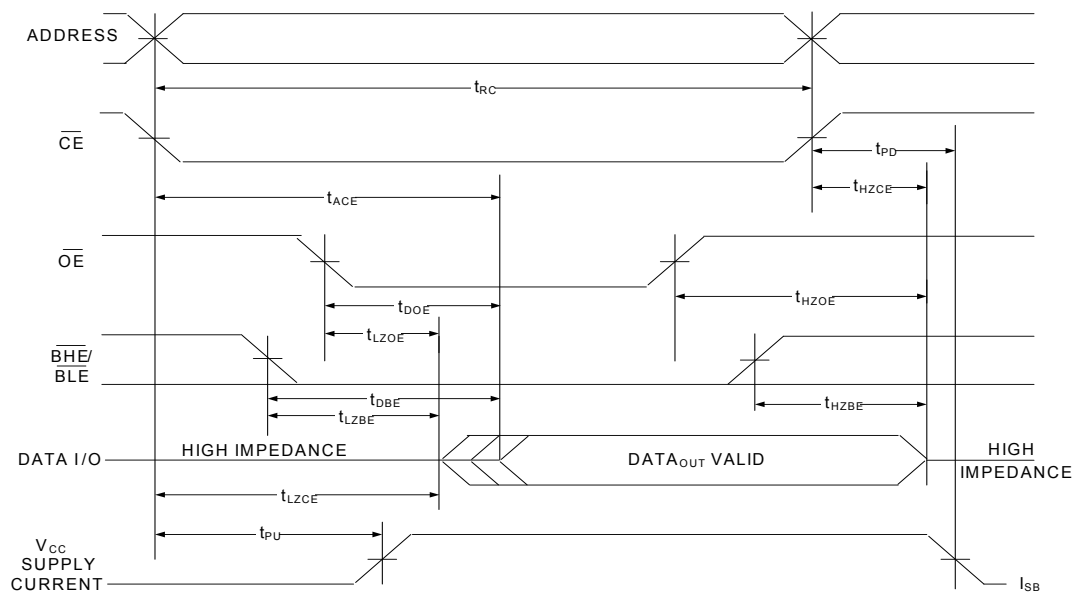
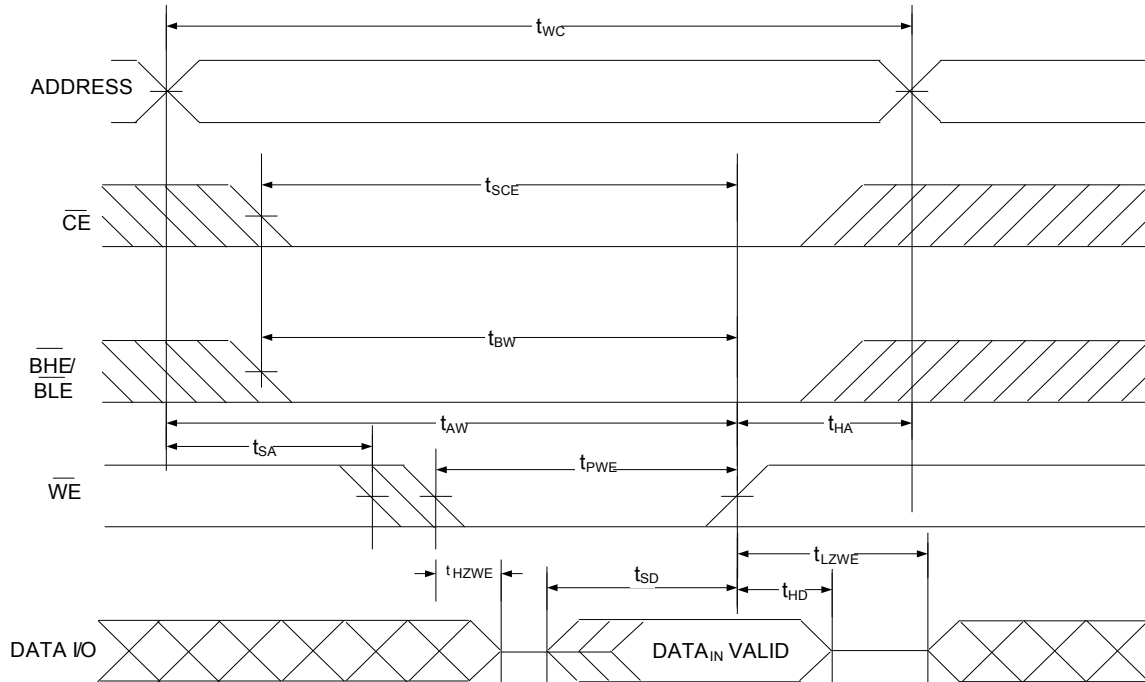


Figure 5. Read Cycle No. 2 (\overline{OE} Controlled) [21, 22]



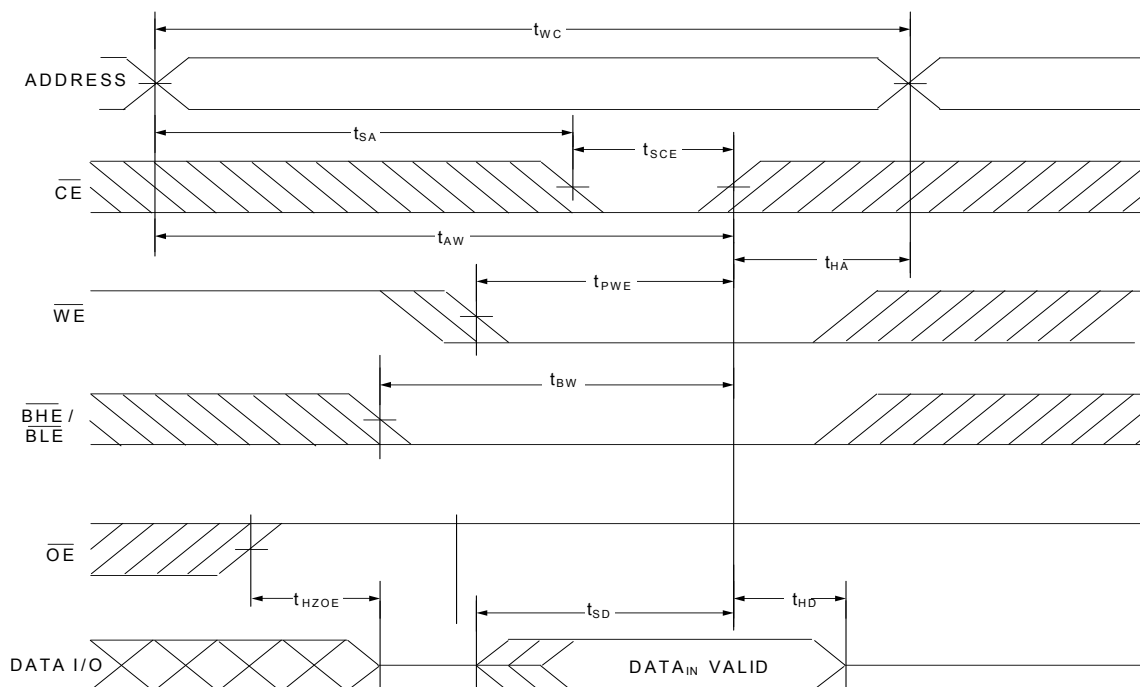
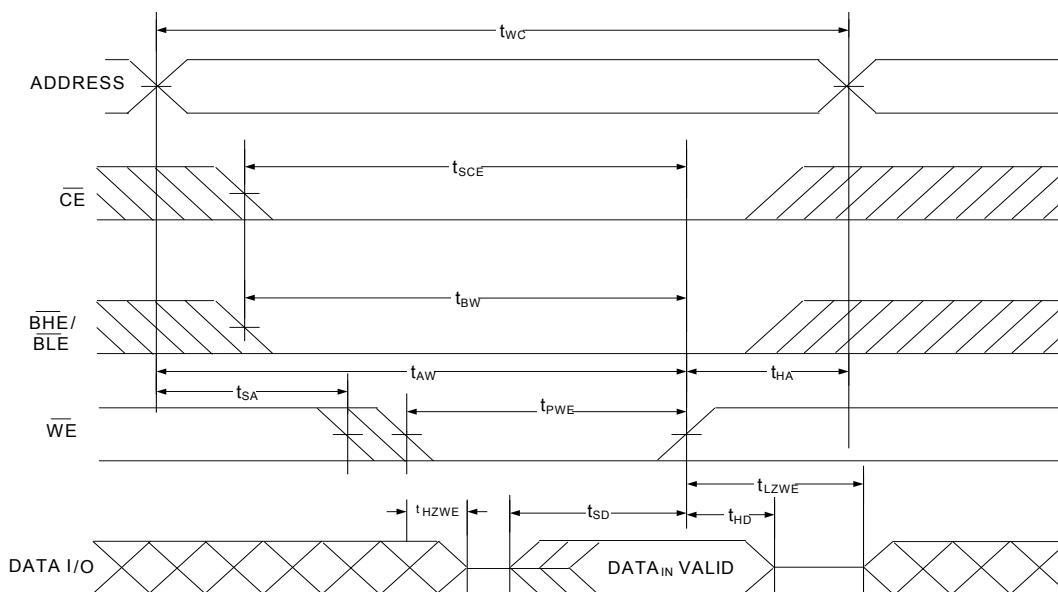
Notes

20. The device is continuously selected. $\overline{OE} = V_{IL}$, $\overline{CE} = V_{IL}$, \overline{BHE} or \overline{BLE} or both = V_{IL} .
21. \overline{WE} is HIGH for Read cycle.
22. Address valid prior to or coincident with \overline{CE} LOW transition.

Switching Waveforms (continued)
Figure 6. Write Cycle No. 1 ($\overline{\text{WE}}$ Controlled) [23, 24]

Notes

23. The internal write time of the memory is defined by the overlap of $\overline{\text{WE}} = V_{\text{IL}}$, $\overline{\text{CE}}_1 = V_{\text{IL}}$, $\overline{\text{BHE}}$ or $\overline{\text{BLE}}$ or both = V_{IL} , and $\text{CE}_2 = V_{\text{IH}}$. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.

24. Data I/O is in a HI-Z state if $\overline{\text{CE}} = V_{\text{IH}}$, or $\overline{\text{OE}} = V_{\text{IH}}$ or $\overline{\text{BHE}}$, and/or $\overline{\text{BLE}} = V_{\text{IH}}$.

Switching Waveforms (continued)
Figure 7. Write Cycle No. 2 ($\overline{\text{CE}}$ Controlled) [25, 26]

Figure 8. Write Cycle No. 3 ($\overline{\text{WE}}$ Controlled, $\overline{\text{OE}}$ LOW) [25, 26, 27]

Notes

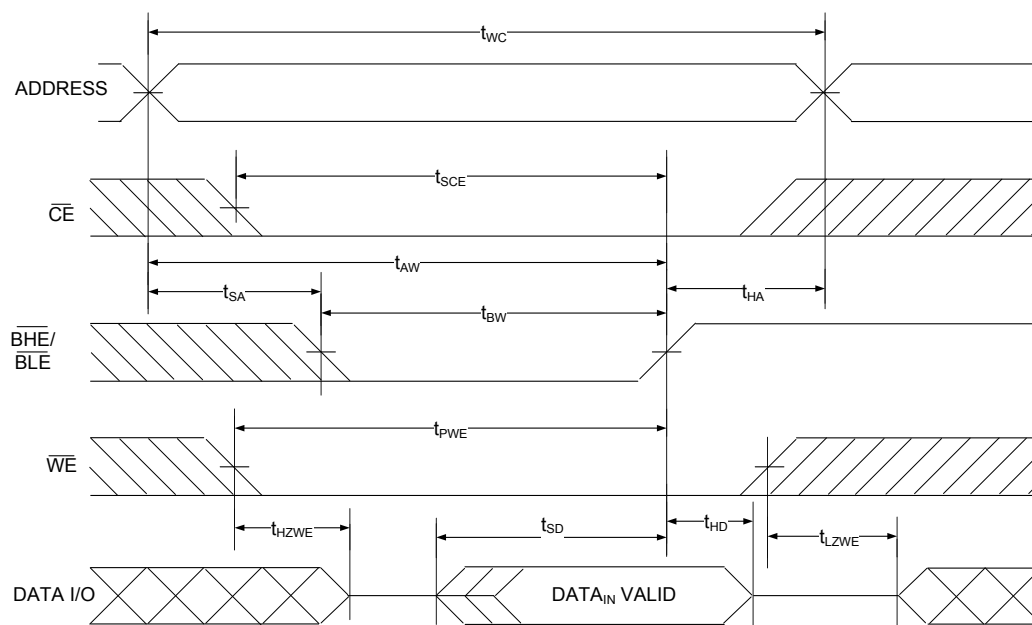
25. The internal write time of the memory is defined by the overlap of $\overline{\text{WE}} = V_{IL}$, $\overline{\text{CE}}_1 = V_{IL}$, $\overline{\text{BHE}}$ or $\overline{\text{BLE}}$ or both = V_{IL} , and $\text{CE}_2 = V_{IH}$. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.

26. Data I/O is in HI-Z state if $\overline{\text{CE}} = V_{IH}$, or $\overline{\text{OE}} = V_{IH}$ or $\overline{\text{BHE}}$, and/or $\overline{\text{BLE}} = V_{IH}$.

27. The minimum write pulse width for Write Cycle No. 3 ($\overline{\text{WE}}$ Controlled, $\overline{\text{OE}}$ LOW) should be sum of t_{HZE} and t_{SD} .

Switching Waveforms (continued)

Figure 9. Write Cycle No. 4 ($\overline{\text{BHE}}/\overline{\text{BLE}}$ Controlled) [28, 29]



Notes

28. The internal write time of the memory is defined by the overlap of $\overline{\text{WE}} = V_{IL}$, $\overline{\text{CE}}_1 = V_{IL}$, $\overline{\text{BHE}}$ or $\overline{\text{BLE}}$ or both = V_{IL} , and $\text{CE}_2 = V_{IH}$. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.

29. Data I/O is in a HI-Z state if $\overline{\text{CE}} = V_{IH}$, or $\overline{\text{OE}} = V_{IH}$ or $\overline{\text{BHE}}$, and/or $\overline{\text{BLE}} = V_{IH}$.

Truth Table – CY62146G

$\overline{\text{CE}}$	$\overline{\text{WE}}$	$\overline{\text{OE}}$	$\overline{\text{BHE}}$	$\overline{\text{BLE}}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	HI-Z	Deselect/Power-down	Standby (I_{SB})
X ^[30]	X	X	H	H	HI-Z	Output disabled	Active (I_{CC})
L	H	L	L	L	Data Out (I/O_0 – I/O_{15})	Read	Active (I_{CC})
L	H	L	H	L	Data Out (I/O_0 – I/O_7); HI-Z (I/O_8 – I/O_{15})	Read	Active (I_{CC})
L	H	L	L	H	HI-Z (I/O_0 – I/O_7); Data Out (I/O_8 – I/O_{15})	Read	Active (I_{CC})
L	H	H	X	X	HI-Z	Output disabled	Active (I_{CC})
L	L	X	L	L	Data In (I/O_0 – I/O_{15})	Write	Active (I_{CC})
L	L	X	H	L	Data In (I/O_0 – I/O_7); HI-Z (I/O_8 – I/O_{15})	Write	Active (I_{CC})
L	L	X	L	H	HI-Z (I/O_0 – I/O_7); Data In (I/O_8 – I/O_{15})	Write	Active (I_{CC})

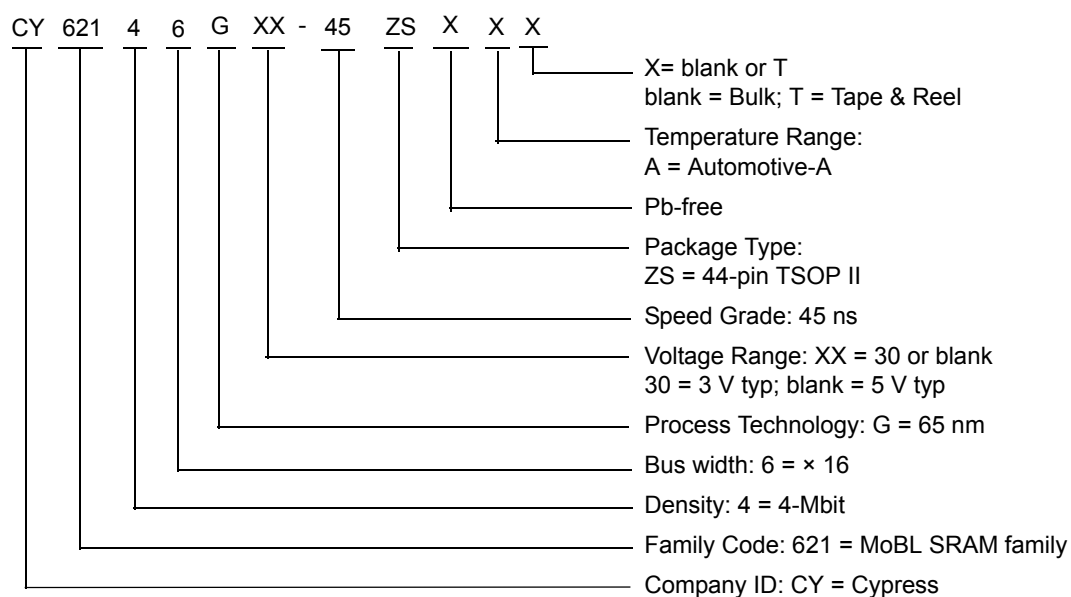
Notes

30. The 'X' (Don't care) state for the chip enables refer to the logic state (either HIGH or LOW). Intermediate voltage levels on these pins is not permitted.

Ordering Information

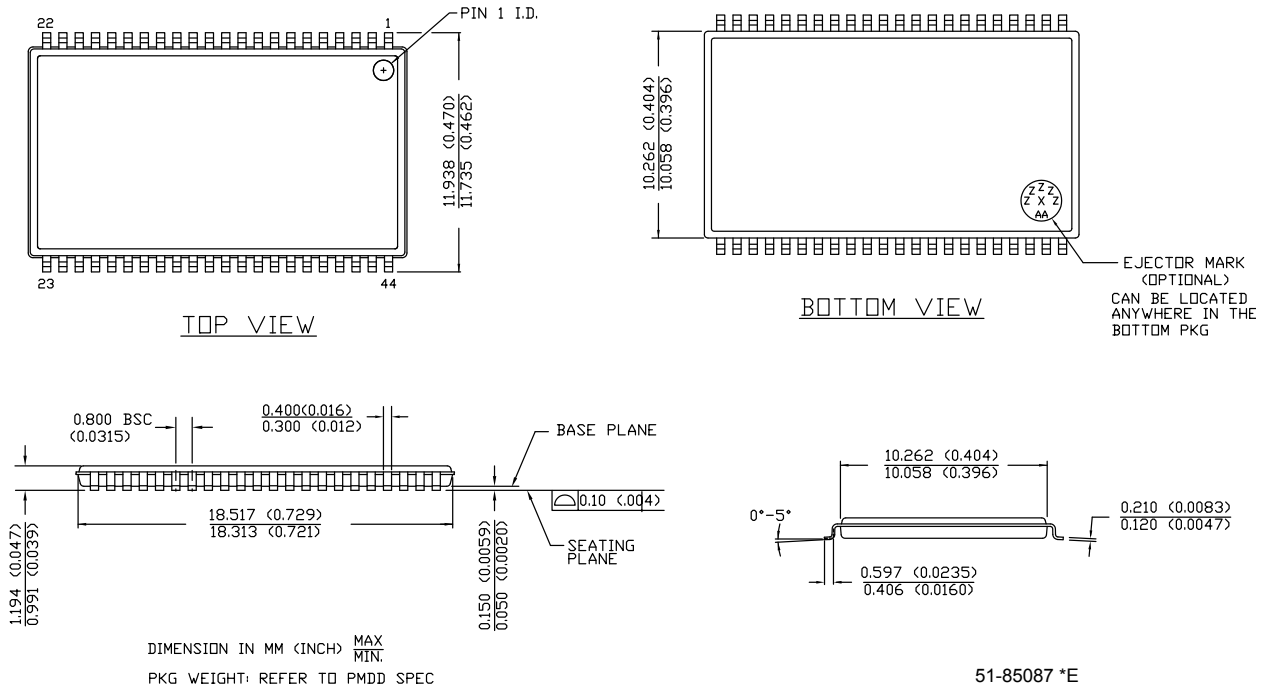
Speed (ns)	Voltage Range	Ordering Code	Package Diagram	Package Type	Operating Range
45	2.2 V–3.6 V	CY62146G30-45ZSXA	51-85087	44-pin TSOP II	Automotive-A
		CY62146G30-45ZSXAT	51-85087	44-pin TSOP II, Tape & Reel	
	4.5 V–5.5 V	CY62146G-45ZSXA	51-85087	44-pin TSOP II	
		CY62146G-45ZSXAT	51-85087	44-pin TSOP II, Tape & Reel	

Ordering Code Definitions



Package Diagrams

Figure 10. 44-pin TSOP Z44-II Package Outline, 51-85087



Acronyms

Acronym	Description
BHE	Byte High Enable
BLE	Byte Low Enable
CE	Chip Enable
CMOS	Complementary Metal Oxide Semiconductor
I/O	Input/Output
OE	Output Enable
SRAM	Static Random Access Memory
TSOP	Thin Small Outline Package
VFBGA	Very Fine-Pitch Ball Grid Array
WE	Write Enable

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
μA	microampere
μs	microsecond
mA	milliampere
mm	millimeter
ns	nanosecond
Ω	ohm
%	percent
pF	picofarad
V	volt
W	watt

Document History Page

Document Title: CY62146G MoBL [®] Automotive, 4-Mbit (256K words × 16 bit) Static RAM with Error-Correcting Code (ECC) Document Number: 002-03594				
Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change
*A	5035945	NILE	12/09/2015	Changed status from Preliminary to Final.
*B	5427239	NILE	09/23/2016	Updated Features : Added "AEC-Q100 qualified". Updated Maximum Ratings : Updated Note 4 (Replaced "2 ns" with "20 ns"). Updated DC Electrical Characteristics : Changed minimum value of V _{OH} parameter from 2.2 V to 2.4 V corresponding to Operating Range "2.7 V to 3.6 V" and Test Condition "V _{CC} = Min, I _{OH} = -1.0 mA". Changed minimum value of V _{IH} parameter from 2.0 V to 1.8 V corresponding to Operating Range "2.2 V to 2.7 V". Updated Ordering Information : Updated part numbers. Updated to new template. Completing Sunset Review.
*C	5975694	AESATMP8	11/24/2017	Updated logo and Copyright.

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